N on-adiabatic K ohn-anom aly in a doped graphene m onolayer

M ichele Lazzeri and Francesco M auri

IM PM C, Universites Paris 6 et 7, CNRS, IPGP, 140 rue de Lourm el, 75015 Paris, France

(Dated: April 15, 2024)

We compute, from rst-principles, the frequency of the E_{2g} , phonon (R am an G band) of graphene, as a function of the charge doping. Calculations are done using i) the adiabatic Born-O ppenheim er approximation and ii) time-dependent perturbation theory to explore dynamic e ects beyond this approximation. The two approaches provide very dienent results. W hile, the adiabatic phonon frequency weakly depends on the doping, the dynamic one rapidly varies because of a K ohn anomaly. The adiabatic approximation is considered valid in most materials. Here, we show that doped graphene is a spectacular example where this approximation miserably fails.

PACS num bers: 71.15 M b, 63.20 K r, 78.30 N a, 81.05 J w

Graphene is a 2-dimensional plane of carbon atoms arranged in a honeycom b lattice. The recent dem onstration of a eld-e ect transistor (FET) based on a fewlayers graphene sheet has boosted the interest in this system [1, 2, 3]. In particular, by tuning the FET gatevoltage V_q it is possible to dope graphene by adding an excess surface electron charge. The actual possibility of building a FET with just one graphene monolayer maxim izes the excess charge corresponding to a single atom in the sheet. In a FET -based experiment, graphene can be doped up to 3 10¹³ cm² electron concentration [1, 2], corresponding, in a monolayer, to a 0.2% valence charge variation. The resulting chem ical-bond modi cation could induce a variation of bond-lengths and phonon-frequencies of the same order, which would be measurable. This would realize the dream of tuning the chem istry, within an electronic device, by varying V_g.

The presence of Kohn anomalies (KAs) [4, 5] in graphene could act as a magnifying glass, leading to a variation of the optical phonon-frequencies much larger than the 0.2% expected in conventional systems. On the other hand, the phonon-frequency change induced by FET-doping could provide a much more precise determ ination of the KA, with respect to other experim ental settings. KAs manifest as a sudden change in the phonon dispersion for a wavevector q $2k_{\rm F}$, where $k_{\rm F}$ is a Ferm i-surface wavevector [4]. The KA can be determ ined by studying the phonon frequency as a function of q by, e.g., inelastic x-ray, or neutron scattering. These techniques have a nite resolution, in q and energy, which lim its the precision on the measured KA dispersion. In graphene, $2k_F$ is proportional to V_q . This suggests an alternative way to study the KA, that is to measure the phonon frequency at a xed q and to vary $2k_F$ by changing Vg.W ithin this approach, one could use R am an scattering, which has a much better energy and momentum resolution than x-ray and neutron scattering. This approach is feasible for graphene, which has a KA for the Ram an-active E_{2q} -phonon [5] (Ram an G-band).

In this paper, we compute the variation of phonon frequency of the Raman G-band (E $_{\rm 2g}$ mode at $\)$

in a graphene monolayer, as a function of the Fermi level. First, the calculations are done using a fully abinitio approach within the custom ary adiabatic Born-Oppenheimer approximation. Then, time-dependent perturbation theory (TDPT) is used to go beyond.

Ab-initio calculations are done within density functional theory (DFT), using the functional of Ref. [6], plane waves (30 Ry cuto) and pseudopotentials [7]. The Brillouin zone (BZ) integration is done on a uniform 64 64 1 grid. An electronic sm earing of 0.01 Ry with the Ferm i-D irac distribution is used [8]. The twodim ensional graphene crystal is simulated using a supercell geometry with an interlayer spacing of 7.5 A (if not otherwise stated). Phonon frequencies are calculated within the approach of Ref. [9], using the PW SCF code [10]. The Ferm i-energy shift is simulated by considering an excess electronic charge which is compensated by a uniform ly charged back-ground.

The dependence of the Ferm ienergy $_{\rm F}$ on the surface electron-concentration is determined by DFT (Fig 1). In graphene, the gap is zero only for the two equivalent K and K'BZ-points and the electron energy can be approximated as $_{=}$ (K + k) = k for the and bands, where k is a small vector. W ithin this approximation, at T = 0 K temperature

= sign (_F)
$$\frac{\frac{2}{F}}{2}$$
 = sign (_F) $\frac{\frac{2}{F}}{eV^2}$ 10:36 10¹³ cm⁻² (1)

where = 5:52 eV A from DFT, sign (x) is the sign of x and F = 0 at the bands crossing. We remark that, from F ig 1, the typical electron-concentration obtained in experiments [1, 2] corresponds to an important Ferm i-level shift (0.5 eV). For such shift, the linearized bands are still a good approximation (Fig. 1).

The dependence of the graphene lattice-spacing a on , a(), is obtained by minim izing F (;A) = \mathbb{E} (;A) E (0;A₀)=A with respect to A, where E (;A) is the energy of the graphene unit-cell, A is unit-cell area and A₀ = 5:29 A² is the equilibrium A [11] at zero . E (;A) is computed by DFT letting the inter-layer spacing, L, tend to in nity in order to elim inate the spurious interac-

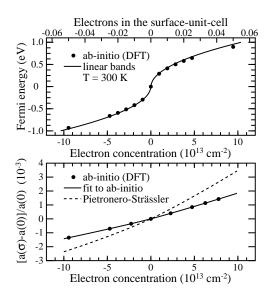


FIG.1: G raphene m onolayer. Upper panel: $_{\rm F}$ as a function of the surface electron-concentration from DFT calculations and from linearized bands (at T = 300 K). Lower panel: in-plane lattice spacing a as a function of . The tting function is Eq.2 and the dashed line is from Ref. [13].

tion between the background and the charged sheet [12]. a() = [a() a(0)]=a(0) was determined in Ref. [3] for intecalated graphite on the basis of a semiem piricalmodel. Using the same functional dependence as in Ref. [13], our DFT calculations are tted by

$$a() = 6:748 \quad 10^{6} j j^{3=2} + 1:64 \quad 10^{6} ;$$
 (2)

where is in units of 10^{13} cm². W ith = $3 \ 10^{13}$ cm², the lattice spacing variation is 0.05%, which is, as expected, of the same order of the valence-charge variation.

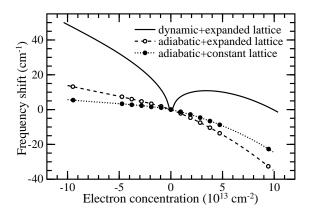


FIG. 2: Frequency of the E_{2g} phonon (Raman G band) as a function of : shift with respect to the zero-doping frequency. Calculations are done using standard DFT (adiabatic) or TDPT (dynamic), keeping the lattice-spacing constant (constant lattice) or varying it according to Eq. 2 (expanded lattice). Points are DFT calculations. D ashed line is from Eq. 3. Experiments should be compared with the continuous line.

The frequency of the E_{2g} phonon is computed by static perturbation theory of the DFT energy [9], i.e. from the linearized forces acting on the atom s due to the static displacement of the other atom s from their equilibrium positions. This approach is based on the adiabatic B om-O ppenheim erapproximation, which is the standard textbook approach for phonon calculations and is always used, to our know ledge, in the ab-initio frequency calculations. The computed zero-doping phonon frequency is $!_a^0 = (2 \text{ c}) = 1554 \text{ cm}^{-1}$, where c is the speed of light. The frequency variation ! with is reported in Fig. 2. Calculations are done keeping the lattice-spacing constant at a (0), or varying it according to Eq. 2. In this latter case, ! is tted by

$$\frac{!}{2 c} = 2.13 \quad 0.0360^2 \quad 0.00329^3 \quad 0.226j j^{=2}; (3)$$

where is in 10^{13} cm² and !=(2 c) is in cm¹ units. The lattice-parameter variation is important, since it nearly doubles the frequency shift. However, Fig. 2 does not show the sudden increase of the phonon frequency with j j expected from the displacement of the KA wavevector with the doping. In particular, for = $3 10^{13}$ cm², the frequency variation is 0.5%, which excludes a magnic cation e ect related to the KA.

It is important to understand whether the absence of the KA is an artifact of the adiabatic approximation, used so far. Thus, we consider that a phonon is not a static perturbation but a dynam ic one, oscillating at the frequency !, which can be treated within time-dependent perturbation theory. U sing such dynam ic approach in the context of DFT [14], the dynam icalmatrix of a phonon with momentum q, projected on the phonon normalcoordinate is

$$D_{q}^{F} (!) = F_{q}^{F} (!) + n(r)^{2} V^{b}(r) d^{3}r$$

$$Z$$

$$n_{q}(r) K(r; r^{0}) n_{q}(r^{0}) d^{3}r d^{3}r^{0}; (4)$$

where n (r) is the charge density, ${}^{2}V^{b}$ is the second derivative of the bare (purely-ionic) potential with respect to the phonon displacement, n is the derivative of n, K (r; r⁰) = ${}^{2}E_{\rm H xc}$ [n]=(n(r) n(r)), $E_{\rm H xc}$ [n] is the Hartree and exchange-correlation functional, and

$$F_{q}^{F}(!) = \frac{2}{N_{k}} \frac{X}{_{knm}} \frac{\oint_{(k+q)m, kn} \hat{f}[f_{(k+q)m} - f_{kn}]}{_{(k+q)m} - _{kn} + -! + i}$$
(5)

Here a factor 2 accounts for spin degeneracy, the sum is performed on N_k wavevectors, D_{(k+q)m;kn} = h(k + q)m j V kni is the electron-phonon coupling (EPC), V is the derivative of the Kohn-Sham poten-tial, kni is a B loch eigenstate with wavevector k, band index n and energy $_{kn}$, $f_{kn} = f_T (_{kn} _F)$, where f_T is the Ferm i-D irac distribution and is a sm all real number.

Im posing ! = 0 and = 0 in Eq.4, one obtains the standard adiabatic approxim ation [9] and the phonon frequency is $!_a^{F} = \overline{D_q^{F}(0)} = M$, where M is the atom ic mass. In the dynamic case, ! has to be determined selfconsistently from $! = D_q^F$ (!)=M. However, considering dynamic and doping e ects as perturbations, at the low est order one can insert the adiabatic zero-doping phonon frequency $!_a^0$ in Eq 4 and obtain the real part of the dynam ic frequency from $!_d^F = < e^F D_q^F (!_a^0) = M$.

Let us consider the $q! 0 \lim it in Eq. 5$. In the adiabatic case

$$F_{0}^{F}(0) = \frac{2}{N_{k}} \frac{X}{k;n \in m} \frac{p_{km;kn} f_{km}}{km} \frac{f_{kn}}{kn} - \frac{2}{N_{k}} \frac{X}{k;n \in m} \frac{p_{km;kn} f_{km}}{km} \frac{f_{kn}}{kn} - \frac{2}{N_{k}} \frac{X}{k;n} p_{kn;kn} f_{T}(kn + F); \quad (6)$$

where $T(x) = df_T(x) = (dx)$. In the dynamic case

$$F_{0}^{F}(!_{a}^{0}) = \frac{2}{N_{k}} \frac{X}{k; n \in m} \frac{\mathcal{D}_{km;kn} \hat{\mathcal{I}}[f_{km} \quad f_{kn}]}{km \quad kn + \sim !_{a}^{0} + i}$$
(7)

In Eq. 6 (adiabatic case), there are two contributions, the rst from inter-band and the second from intra-band transitions (depending on $_{\rm T}$ and proportional to the density of states at $_{\rm F}$). On the contrary, in Eq.7 (dynam ic case) only inter-band transitions contribute.

The variation of ! F w ith F is

$$! = ! F !^{0} ' \frac{D F D^{0}}{2M !_{0}^{0}}; \qquad (8)$$

 $!_{a}^{0}$. The presence of a where is assumed that ! K ohn anom aly is associated to a singularity in the electron screening, which, within the present form alism, can occur if the denom inator of Eq.5 approaches zero, i.e. for electronsnearthe Fermilevel. Let us call F (!) the part of F_0^F (!) obtained by restricting the k-sum on a circle of radius k centered on K, with $(k j_F j \sim !_a^0)$ k_BΤ. The anomalous ! is obtained by substituting D with F [15] in Eq.8

$$!_{a} = \frac{F^{*_{F}}(0) F^{*0}(0)}{\frac{1}{2} 2M !_{a}^{0}}$$
(9)

$$!_{d} = \langle e | \frac{F^{F}(!_{a}^{0}) - F^{0}(!_{a}^{0})}{2M !_{a}^{0}}$$
 (10)

in the adiabatic $(!_a)$ and dynamic $(!_d)$ cases. An analytic expression for F is obtained by i) linearizing the band dispersion; ii) writing the EPC as $\mathcal{D}_{(K+k)n;(K+k)m} \hat{\mathcal{J}} = hD^{2}i[1]$ $\cos(2)$, where is the angle between the phonon-polarization and k, the sign

depends on the transition (see Eq. 6 and note 24 of Ref. [5]) and hD² i_{p} 45:6 (eV)²/A² from DFT [16]; iii) substituting $1=N_k$, with $2A_0=(2)^2$ d²k in Eqs. 6-7, a factor 2 counts K and K ', and k is measured from K .

In the adiabatic case

$$F^{F_{F}}(0) = \begin{cases} Z_{k} \\ kdk \\ 0 \\ T(k_{F}) \\ T(k_{F}) \\ T(k_{F}) \\ T(k_{F}) \end{cases} (k_{F})g; (11)$$

where = $2A_0hD^2$ i= . Substituting Eq. 11 into Eq. 9 one obtains $!_a$. At any T, $!_a = 0$. This result is not trivial and com es from the exact cancellation of the inter-band (to , rst line of Eq.11) to , second line of and intra-band (to and Eq. 11). For example, at T = 0, both contributions to ~ $!_a$ are large and equal to $"j_F j$ and $"j_F j$ respectively, where $^{0} = \sim = (2M ! a^{0}) = 4:43 10^{3}$ and 0 =(2 ~c) = 35:8 cm 1 =(eV). Concluding, an adiabatic calculation of ! F does not show any singular behavior in $_{\rm F}$ related to the Kohn anom aly, in agreement with the state-of-the-art adiabatic DFT calculations of Fig. 2. In the dynam ic case

$$\mathbf{F}^{F}(!_{a}^{0}) = \frac{\sum_{k}^{k} \frac{\mathbf{f}_{T}(k_{F}) \mathbf{f}_{T}(k_{F})}{2 k + \sim !_{a}^{0} + 1} \mathbf{\dot{f}_{J}} \mathbf{\dot{f}_{J}} \mathbf{\dot{f}_{I}};$$
(12)

Substituting Eq. 12 into Eq. 10, for T = 0,

$$\sim !_{d} = {}^{0}j_{F}j_{F} + \frac{}{4}{}^{0}u_{a} \ln \frac{j_{F}j}{j_{F}j_{F}} + \frac{}{2}{}^{1}\frac{}{2}{2}}{}^{1} : (13)$$

In this case, the situation is very di erent since the large inter-band contribution is not canceled by an intra-band term . In particular, there are two logarithm ic divergences for $_{\rm F} = -!_{\rm a}^{0} = 2$ and for $j_{\rm F} j - !_{\rm a}^{0} = 2$ the frequency increases as ⁰j_Fj.

! d computed in this way takes into account transitions between states close to the Fermi level. However, the frequency is also a ected by the variation of the lattice-spacing, by the transitions involving a state far from $_{\rm F}$ and by the second and third term s in Eq. 4. All these contributions are accurately described by our adiabatic DFT calculations. Therefore, to compare with experiments, we add $!_d$ to the adiabatic DFT frequency shift of Eq. 3. The results are shown in Fig. 2 for T = 300 K, and in Fig.3 as a function of T for a smaller range. Even at room temperature, the non-adiabatic Kohn anom aly magni esthee ectof the doping and for a valence-charge variation of -0.2% (+ 0.2%), the frequency varies by +1.5% (+0.7%). ! is asymmetric with respect to $_{\rm F}$ and has a maximum for $+3.510^{13}$ cm 2 . Since $!_{\rm d}$ is an even function of $_{\rm F}$, this lack of electron-hole sym m etry is entirely due to the adiabatic DFT contribution. The $_{\rm F} = -2$ logarithm is a nom alies are visible at T = 4 and 70 K. The presence of a logarithm ic KA in this two-dimensional system is quite remarkable since such divergences are typical of one-dim ensional system s. They are present in graphene because of its particular m assless D irac-like electron band dispersion.

Finally, the Ram an G-band has a nite hom ogeneous linew idth due to the decay of the phonon into electronhole pairs. Such EPC broadening can be obtained either from the imaginary part of the TDPT dynam ical matrix (Eq. 12) or, equivalently, from the Ferm igolden rule [16]:

$$= \frac{\frac{1}{a} \frac{1}{a}}{2 2 c} \int_{c}^{0} f_{T} \frac{\frac{1}{a}}{2} F_{F} f_{T} \frac{\frac{1}{a}}{2} F$$
(14)

where is the full-width halfmaximum (FW HM) in cm 1 . At T = 0 and $_{\rm F}$ = 0, one recovers the result of Ref. [16], = 11.0 cm 1 . The phonon-phonon scattering contribution to the FW HM is smaller ($1\,{\rm cm}^{-1}$ [17]) and independent of $_{\rm F}$. The totalhom ogeneous FW HM is reported in Fig. 3. The FW HM displays a strong doping dependence; it suddenly drops for j j $0.1\,10^{13}$ cm 2 (j_F j $0.1\,{\rm eV}$). Indeed, because of the energy and momentum conservation, a phonon decays into one electron (hole) with energy $\sim!_a^0=2$ above (below) the level crossing. At T = 0K such process is compatible with the Pauli exclusion-principle only if j_F j $< !_a^0=2$.

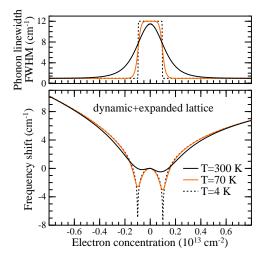


FIG.3: (Color online) Linewidth and dynamic frequency of the E_{2q} mode (Ram an G band). See the caption of Fig.1.

Concluding, a K ohn anom aly dictates the dependence of the highest optical-phonon on the wavevector q, in undoped graphene [5]. Here, we studied the impact of such anom aly on the q = 0 phonon, as a function of the charge-doping .We computed, from rst-principles, the phonon frequency and linewidth of the E_{2g} , phonon (Ram an G band) in the -range reached by recent FET experiments. Calculations are done using i) the custom ary adiabatic Bom-Oppenheim er approximation and ii) tim e-dependent perturbation theory to explore dynam ic e ects beyond this approximation. The two approaches provide very di erent results. The adiabatic phonon frequency displays a sm ooth dependence on and it is not a ected by the K ohn anom aly. O n the contrary, when dynam ice ects are included, the phonon frequency and lifetime display a strong dependence on , due to the K ohn anom aly. The variation of the R am an G-band with the doping in a graphene-FET has been recently measured by two groups [18, 19]. Both experiments are well described by our dynam ic calculation but not by the more approxim ate adiabatic one. We remark that the adiabatic B om-O ppenheim er approximation is considered valid in most materials and is commonly used for phonon calculations. Here, we have shown that doped graphene is a spectacular example where this approximation miserably fails.

W e aknowledge useful discussions with A M. Saitta, A \mathcal{L} . Ferrari and S. P iscanec. Calculation were done at ID R IS (O rsay, France), project n° 061202.

- [L] K.S. Novoselov et al. Science 306, 666 (2004); K.S. Novoselov et al. Nature 438, 197 (2005).
- [2] Y. Zhang, Y W . Tan, H L. Storm er, and P.K in, Nature 438, 201 (2005).
- [3] A.C.Ferrariet al, Phys.Rev.Lett. 97, 187401 (2006).
- [4] W .Kohn Phys.Rev.Lett.2, 393 (1959).
- [5] S. Piscanec, M. Lazzeri, F. Mauri, A.C. Ferrari, and J. Robertson, Phys. Rev. Lett. 93, 185503 (2004).
- [6] J.P. Perdew, K. Burke, and M. Emzerhof Phys. Rev. Lett. 77, 3865 (1996).
- [7] D.Vanderbilt, Phys. Rev. B 41, 7892 (1990).
- [8] M. Methfessel and A. T. Paxton Phys. Rev. B 40, 3616 (1989).
- [9] S. Baroni, S. de Gironcoli, A. Dal Corso, and P. Giannozzi, Rev. M od. Phys. 73, 515 (2001).
- [10] S.Baroniet al. http://www.pwscf.org.
- [11] Consider a graphene sample of N unit-cells, which is in contact with an electrode of area A^e . If N > $A^e = A$, A is obtained by m inim izing the total energy of the sample E (;A) $A^e = A + (N = A^e = A)E(0;A_0)$. This is equivalent to m inim izing F (;A).
- [12] By a simple electrostatic model, the dependence of the cell-energy E on L is E (L)=A = $=6^{2}L + _{0} + _{1}=L + _{2}=L^{2} + 0$ (l=L³). E is computed for L = 7:5;15;22:5;30;37:5 A and the parameters _i, are tted to obtain the limit L ! 1.
- [13] L.Pietronero and S.Strassler Phys. Rev. Lett. 47, 593 (1981).
- [14] Eqs. 4.17a and 4.23 of P B. A llen, in D ynam ical P roperties of Solids, Ed. by G.K. Horton and A A. M aradudin, (N orth-H olland, Am sterdam, 1980), v. 3, p. 95–196.
- [15] The dependence of n on ! $_q$ and $_F$ is neglected, because the functional of Eq.4 is stationary with respect to n. Notice that there are other, equivalent expressions for the dynam icalm atrix which are not stationary in ! $_q$, for which this approximation is not justi ed.
- [16] M. Lazzeri, S. Piscanec, F. Mauri, A C. Ferrari, and J. Robertson, Phys. Rev. B 73, 155426 (2006).
- [17] N.Bonini, M.Lazzeri, F.Mauri, N.Marzari unpublished.
- [18] J.Yan, Y.Zhang, P.K in, and A.Pinczuk (2006), unpublished. Results shown the 28 Sept. 2006 at the G raphene C onference, M ax P lanck Institut, D resden.
- [19] S.Pisana, M. Lazzeri, C. Casiraghi, K.S. Novoselov, A.K.

Geim , A $\mathcal L$.Ferrari, <code>F.M</code> auri, <code>cond-m</code> at/0611714 (2006).